

10/631,098

1-13 (Canceled).

14. (Currently Amended) A silicon over insulator (SOI) metal oxide silicon field effect transistor (MOSFET) device comprising:

a body;

a gate opposite said body;

~~a resistive/capacitor~~ an RC discriminator comprising a resistor and a capacitor, wherein said RC discriminator is connected to said gate at a point of said RC discriminator between said resistor and said capacitor; and

a circuit control network connected to said body, said circuit control network modulating a potential voltage of said body to provide electrostatic discharge (ESD) protection.

15. (Currently Amended) The device in claim 14, wherein said ~~control~~ circuit control network is connected to said gate.

16. (Canceled).

17. (Currently Amended) The device in claim 14, wherein said circuit control network ~~circuit~~ limits said body to a reference voltage.

10/631,098

18. (Currently Amended) The device in claim 14, wherein said ~~control~~ circuit control network comprises at least one SOI MOSFET.

19. (Currently Amended) The device in claim 14, wherein said circuit control network comprises at least one ESD SOI diode.

20. (Currently Amended) The device in claim 14, wherein said circuit control network ~~circuit~~ comprises at least one body/gate-coupled SOI diode.

21. (Canceled).

22. (Currently Amended) The device in claim 14, further comprising:

an input pad connected to said gate;

a drain adjacent said gate; and

a source opposite said drain,

wherein said circuit control network is connected to said input pad and said drain and said source is connected to Vss.

23. (Canceled).

10/631,098

24. (New) A silicon over insulator (SOI) metal oxide silicon field effect transistor (MOSFET) device comprising:

an n-channel SOI MOSFET comprising first body and a first gate opposite said first body;

a p-channel SOI MOSFET connected to said n-channel SOI MOSFET, wherein said p-channel SOI MOSFET comprises a second body and a second gate opposite said second body;

a first RC discriminator comprising a first resistor and a first capacitor, wherein said first RC discriminator is connected to said first gate at a point of said first RC discriminator between said resistor and said capacitor;

a second RC discriminator comprising a second resistor and a second capacitor, wherein said second RC discriminator is connected to said second gate at a point of said second RC discriminator between said resistor and said capacitor;

a first circuit control network connected to said first body, said first circuit control network modulating a potential voltage of said first body to provide electrostatic discharge (ESD) protection; and

a second circuit control network connected to said second body, said second circuit control network modulating a potential voltage of said second body to provide electrostatic discharge (ESD) protection.

25. (New) The device in claim 24, wherein said first circuit control network and said second circuit control network comprise at least one SOI MOSFET.

10/631,098

26. (New) The device in claim 24, wherein said p-channel SOI MOSFET further comprises a first source and a first drain, wherein one of said first source and said first drain is connected to said first resistor and the other of said first source and said first drain is connected to said first capacitor; and

wherein said n-channel SOI MOSFET further comprises a second source and a second drain, wherein one of said second source and said second drain is connected to said second resistor and the other of said second source and said second drain is connected to said second capacitor.

27. (New) The device in claim 24, wherein said first resistor and said first capacitor initiate coupling of said first gate when an overvoltage or overcurrent condition exists; and

wherein said second resistor and said second capacitor initiate coupling of said second gate when an overvoltage or overcurrent condition exists.

28. (New) The device in claim 24, wherein said first circuit control network limits said first body to a reference voltage, and said second circuit control network limits said second body to said reference voltage.

29. (New) The device in claim 24, wherein said first circuit control network and said second control network provide different reference voltages.

10/631,098

30. (New) The device in claim 24, further comprising a pad connected between said n-channel SOI MOSFET and said p-channel SOI MOSFET.

31. (New) A silicon over insulator (SOI) metal oxide silicon field effect transistor (MOSFET) device comprising:

a floating body;

a gate opposite said body;

an RC discriminator comprising a resistive transistor and a capacitor, wherein said RC discriminator is connected to said gate at a point of said RC discriminator between said resistive transistor and said capacitor; and

a circuit control network connected to said body, said circuit control network modulating a potential voltage of said body to provide electrostatic discharge (ESD) protection.

32. (New) The device in claim 31, wherein said circuit control network limits said body to a reference voltage.

33. (New) The device in claim 31, wherein said circuit control network comprises an SOI MOSFET.

10/631,098

34. (New) The device in claim 31, further comprising a source and a drain, wherein one of said source and said drain is connected to said resistive transistor and the other of said source and said drain is connected to said capacitor.

35. (New) The device in claim 31, wherein said resistor and said capacitor initiate coupling of said gate when an overvoltage or overcurrent condition exists.

36. (New) The device in claim 31, further comprising a pad connected to said capacitor.